ZXM61P03F

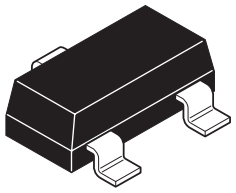
30V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS}$=-30V; $R_{DS(ON)}$=0.35Ω; I_D=-1.1A

DESCRIPTION

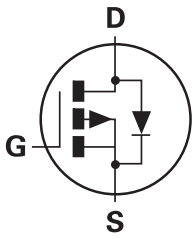
This new generation of high density MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



SOT23

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package



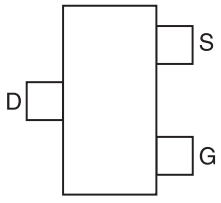
APPLICATIONS

- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control

ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXM61P03FTA	7	8 embossed	3,000
ZXM61P03FTC	13	8 embossed	10,000

Pin out



Top view

DEVICE MARKING

P03

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	±20	V
Continuous Drain Current (V_{GS}=-10V; T_A=25°C)(b) (V_{GS}=-10V; T_A=70°C)(b)	I_D	 -1.1 -0.9	A
Pulsed Drain Current (c)	I_{DM}	-4.3	A
Continuous Source Current (Body Diode)(b)	I_S	-0.88	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	-4.3	A
Power Dissipation at T_A=25°C (a) Linear Derating Factor	P_D	625 5	mW mW/°C
Power Dissipation at T_A=25°C (b) Linear Derating Factor	P_D	806 6.4	mW mW/°C
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	200	°C/W
Junction to Ambient (b)	$R_{\theta JA}$	155	°C/W

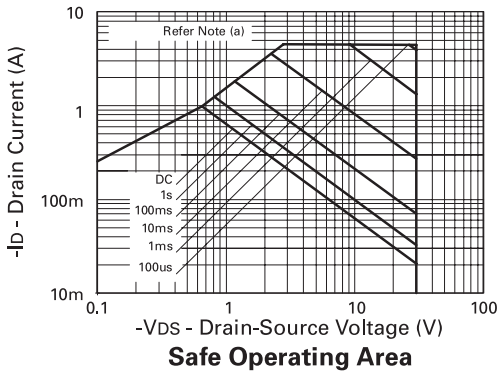
NOTES:

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

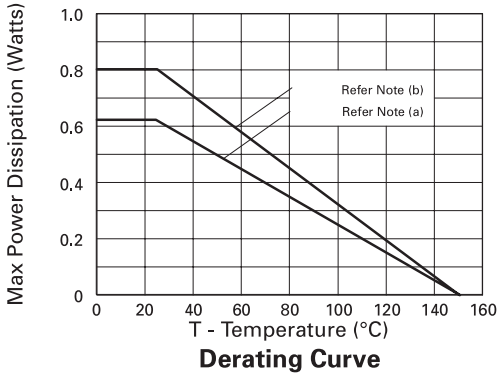
(b) For a device surface mounted on FR4 PCB measured at t≤5 secs.

(c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

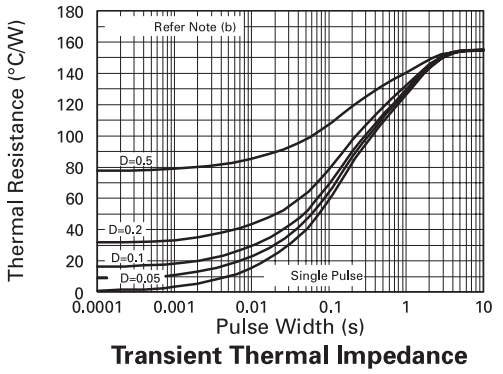
CHARACTERISTICS



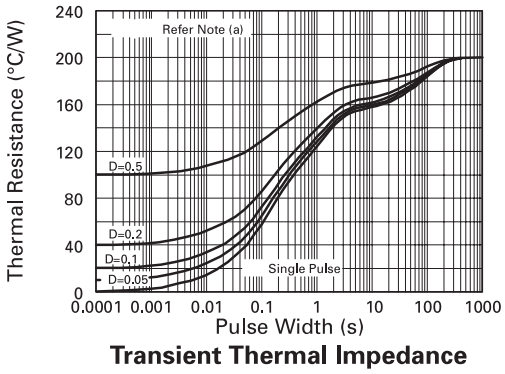
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Transient Thermal Impedance

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30			V	I_D=-250μA, V_{GS}=0V
Zero Gate Voltage Drain Current	I_{DSS}			-1	μA	V_{DS}=-30V, V_{GS}=0V
Gate-Body Leakage	I_{GSS}			±100	nA	V_{GS}=±20V, V_{DS}=0V
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.0			V	I_D=-250μA, V_{DS}= V_{GS}
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.35 0.55	Ω Ω	V_{GS}=-10V, I_D=-0.6A V_{GS}=-4.5V, I_D=-0.3A
Forward Transconductance (3)	g_{fs}	0.44			S	V_{DS}=-10V,I_D=-0.3A
DYNAMIC (3)						
Input Capacitance	C_{iss}		140		pF	V_{DS}=-25 V, V_{GS}=0V, f=1MHz
Output Capacitance	C_{oss}		45		pF	
Reverse Transfer Capacitance	C_{rss}		20		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		1.9		ns	V_{DD} =-15V, I_D=-0.6A R_G=6.2Ω, R_D=25Ω (Refer to test circuit)
Rise Time	t_r		2.9		ns	
Turn-Off Delay Time	$t_{d(off)}$		8.9		ns	
Fall Time	t_f		5.0		ns	
Total Gate Charge	Q_g			4.8	nC	V_{DS}=-24V,V_{GS}=-10V, I_D=-0.6A (Refer to test circuit)
Gate-Source Charge	Q_{gs}			0.62	nC	
Gate Drain Charge	Q_{gd}			1.3	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			-0.95	V	T_j=25°C, I_S=-0.6A, V_{GS}=0V
Reverse Recovery Time (3)	t_{rr}		14.8		ns	T_j=25°C, I_F=-0.6A, di/dt= 100A/μs
Reverse Recovery Charge(3)	Q_{rr}		7.7		nC	

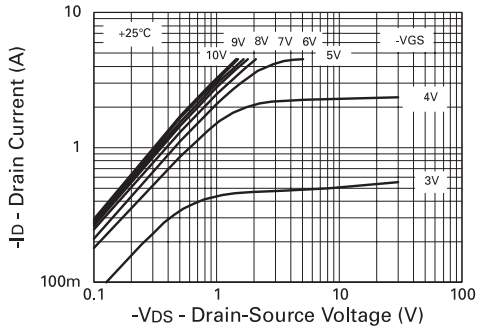
NOTES:

(1) Measured under pulsed conditions. Width=300μs. Duty cycle ≤2%.

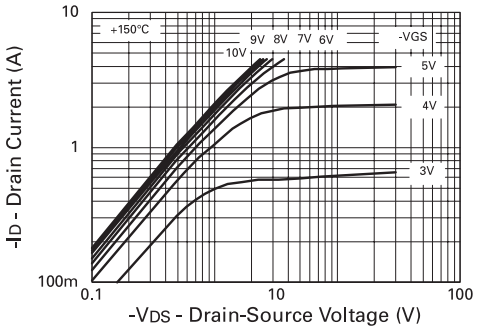
(2) Switching characteristics are independent of operating junction temperature.

(3) For design aid only, not subject to production testing.

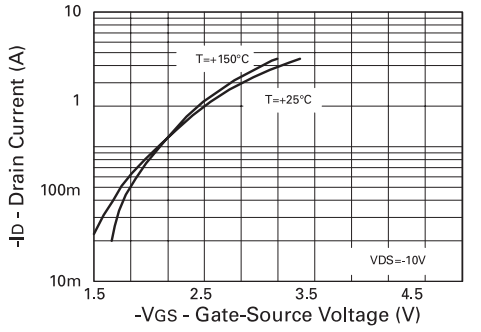
TYPICAL CHARACTERISTICS



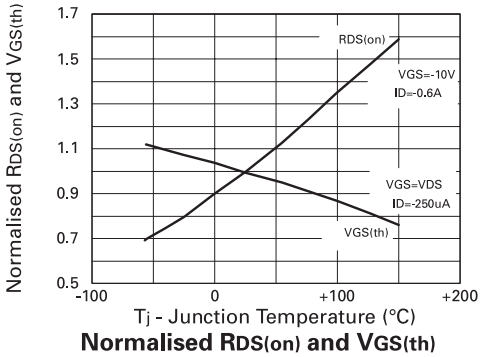
Output Characteristics



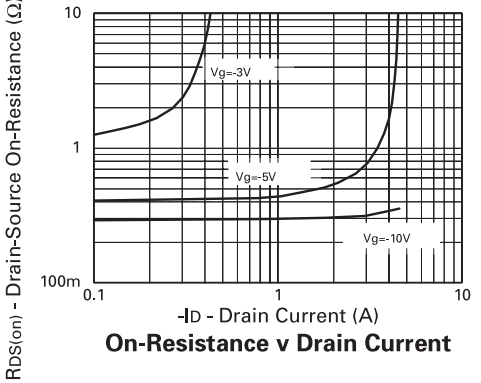
Output Characteristics



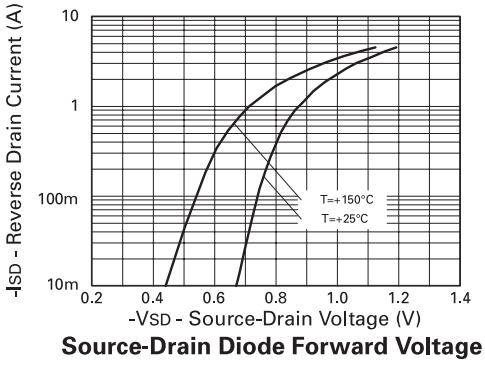
Typical Transfer Characteristics



Normalised RDS(on) and VGS(th) v Temperature

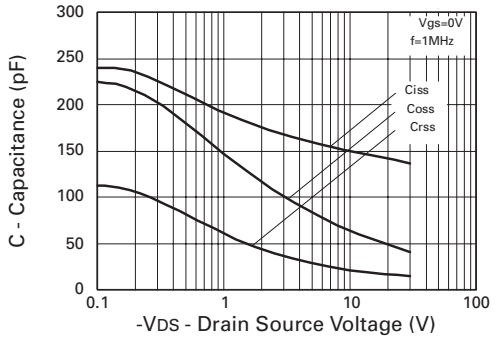


On-Resistance v Drain Current

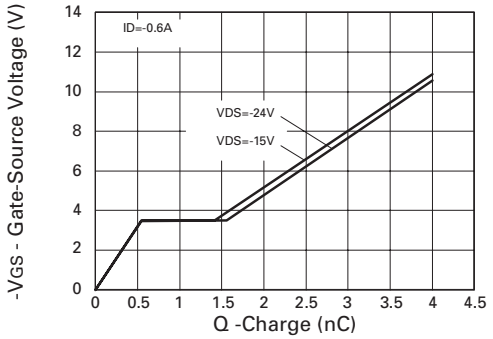


Source-Drain Diode Forward Voltage

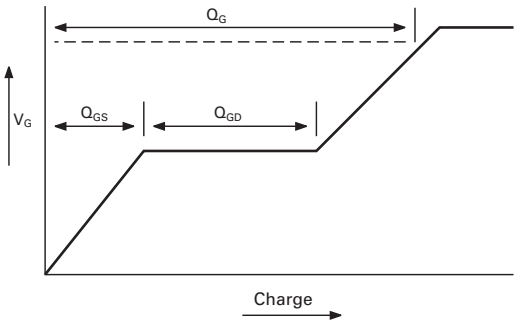
TYPICAL CHARACTERISTICS



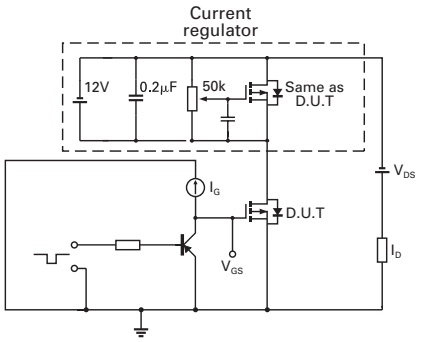
Capacitance v Drain-Source Voltage



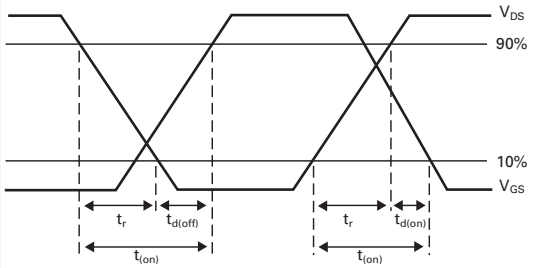
Gate-Source Voltage v Gate Charge



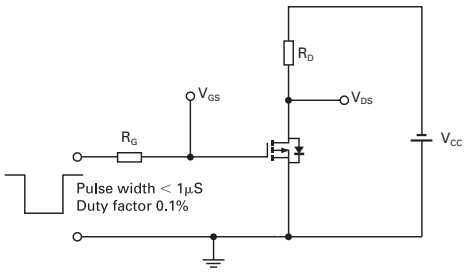
Basic gate charge waveform



Gate charge test circuit

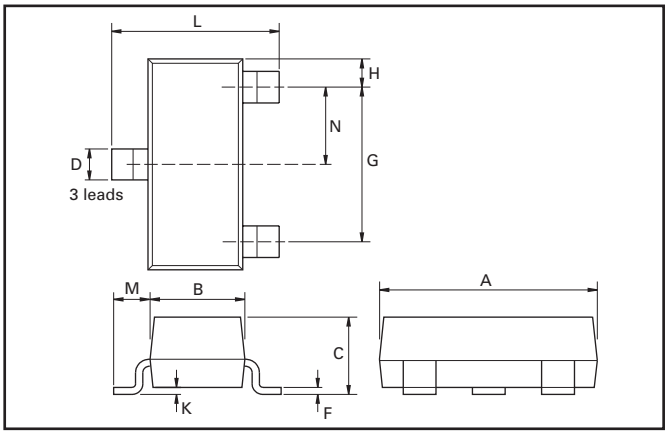


Switching time waveforms

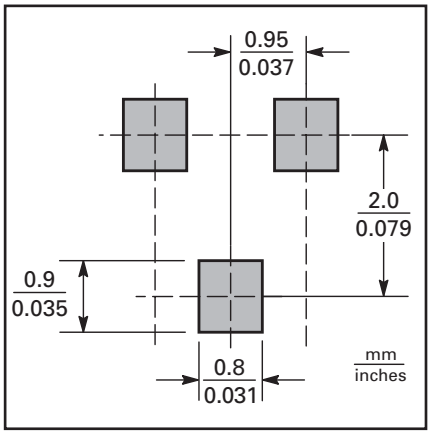


Switching time test circuit

PACKAGE DETAILS



PAD LAYOUT DETAILS



PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Max	Max
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	—	1.10	—	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		—	—		—	

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park Chadderton, Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

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